

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	11	("5374564" "6524935" "6717213" "6852652" "6893936").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:32
L2	195	438/407.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:32
L3	1418	438/197.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:32
L4	166	438/473.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:32
L5	536	438/478.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:33
L6	1118	438/455.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:33
L7	251	438/456.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:33
L8	762	438/458.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:33

L9	886	438/459.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:33
L10	278	438/910.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:33
L11	272	438/933.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:33
L12	2889	257/347.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:33
L13	5	1 and strain\$4 and relax\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:34
L14	7	2 and strain\$4 and relax\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:34
L15	49	3 and strain\$4 and relax\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:34
L16	2	4 and strain\$4 and relax\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:34

L17	54	5 and strain\$4 and relax\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:34
L18	43	6 and strain\$4 and relax\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:34
L19	3	7 and strain\$4 and relax\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:34
L20	33	8 and strain\$4 and relax\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:34
L21	28	9 and strain\$4 and relax\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:34
L22	7	10 and strain\$4 and relax\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:34
L23	52	11 and strain\$4 and relax\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:34
L24	107	12 and strain\$4 and relax\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:35

L25	0	14 and oxide with (adhe\$5 or stick\$3 or mount\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:36
L26	2	15 and oxide with (adhe\$5 or stick\$3 or mount\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:36
L27	0	16 and oxide with (adhe\$5 or stick\$3 or mount\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:36
L28	1	17 and oxide with (adhe\$5 or stick\$3 or mount\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:36
L29	4	18 and oxide with (adhe\$5 or stick\$3 or mount\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:36
L30	1	19 and oxide with (adhe\$5 or stick\$3 or mount\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:36
L31	3	20 and oxide with (adhe\$5 or stick\$3 or mount\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:37
L32	5	21 and oxide with (adhe\$5 or stick\$3 or mount\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:37

L33	0	22 and oxide with (adhe\$5 or stick\$3 or mount\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:37
L34	0	23 and oxide with (adhe\$5 or stick\$3 or mount\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:37
L35	8	24 and oxide with (adhe\$5 or stick\$3 or mount\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:37
L36	2	14 and (second adj (wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:38
L37	3	15 and (second adj (wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:38
L38	0	16 and (second adj (wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:38
L39	7	17 and (second adj (wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:38
L40	17	18 and (second adj (wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:38

L41	3	19 and (second adj (wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:38
L42	12	20 and (second adj (wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:38
L43	13	21 and (second adj (wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:38
L44	1	22 and (second adj (wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:38
L45	4	23 and (second adj (wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:38
L46	12	24 and (second adj (wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:39
L47	2	36 and ("SOI" or (silicon adj on adj insulator))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:39
L48	3	37 and ("SOI" or (silicon adj on adj insulator))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:39

L49	0	38 and ("SOI" or (silicon adj on adj insulator))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:39
L50	6	39 and ("SOI" or (silicon adj on adj insulator))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:39
L51	13	40 and ("SOI" or (silicon adj on adj insulator))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:39
L52	2	41 and ("SOI" or (silicon adj on adj insulator))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:39
L53	11	42 and ("SOI" or (silicon adj on adj insulator))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:40
L54	13	43 and ("SOI" or (silicon adj on adj insulator))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:40
L55	1	44 and ("SOI" or (silicon adj on adj insulator))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:40
L56	4	45 and ("SOI" or (silicon adj on adj insulator))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:40

L57	12	46 and ("SOI" or (silicon adj on adj insulator))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:40
L58	1	47 and (etch\$4 with strain\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:40
L59	3	48 and (etch\$4 with strain\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:40
L60	0	49 and (etch\$4 with strain\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:41
L61	4	50 and (etch\$4 with strain\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:41
L62	3	51 and (etch\$4 with strain\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:41
L63	1	52 and (etch\$4 with strain\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:41
L64	9	53 and (etch\$4 with strain\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:45

L65	4	54 and (etch\$4 with strain\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:41
L66	1	55 and (etch\$4 with strain\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:41
L67	3	56 and (etch\$4 with strain\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:44
L68	8	57 and (etch\$4 with strain\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:42
L69	1	58 and (etch\$4 with strain\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:42
L70	0	47 and (etch\$3 with substrate with relax\$4 same (form\$3 or result or creat\$4) with strain\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:47
L71	0	48 and (etch\$3 with substrate with relax\$4 same (form\$3 or result or creat\$4) with strain\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:47
L72	0	49 and (etch\$3 with substrate with relax\$4 same (form\$3 or result or creat\$4) with strain\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:47

L73	1	50 and (etch\$3 with substrate with relax\$4 same (form\$3 or result or creat\$4) with strain\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:48
L74	1	51 and (etch\$3 with substrate with relax\$4 same (form\$3 or result or creat\$4) with strain\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:48
L75	0	52 and (etch\$3 with substrate with relax\$4 same (form\$3 or result or creat\$4) with strain\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:48
L76	2	53 and (etch\$3 with substrate with relax\$4 same (form\$3 or result or creat\$4) with strain\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:48
L77	2	54 and (etch\$3 with substrate with relax\$4 same (form\$3 or result or creat\$4) with strain\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/01 12:49